

## 1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO-247 plastic package, designed for high frequency switched-mode power supplies. This product is qualified to AEC-Q101 standard for use in automotive applications.



AEC - Q101 Qualified



## 2. Features and benefits

- Highly stable switching performance
- High forward surge capability  $I_{FSM}$
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant
- AEC-Q101 compliant
- High junction operating temperature capability ( $T_{j(max)} = 175\text{ °C}$ )

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

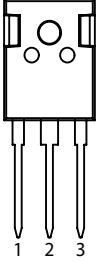
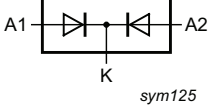
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
<b>Absolute maximum rating</b>						
$V_{RRM}$	repetitive peak reverse voltage		650			V
$I_{O(AV)}$	limiting average output current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 105\text{ °C}$ ; both diodes conducting; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a>	20			A
$T_j$	junction temperature		175			°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; per diode; <a href="#">Fig. 4</a>	-	1.5	1.7	V
		$I_F = 10\text{ A}$ ; $T_j = 150\text{ °C}$ ; per diode; <a href="#">Fig. 4</a>	-	1.8	2.1	V
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 10\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 500\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; per diode; <a href="#">Fig. 6</a>	-	16	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	K	mounting base; connected to cathode		

## 6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
NXPSC20650W-A	TO247	NXPSC20650W-AQ	Tube	30	TO247N	20-Jul-2016

## 7. Marking

Table 4. Marking codes

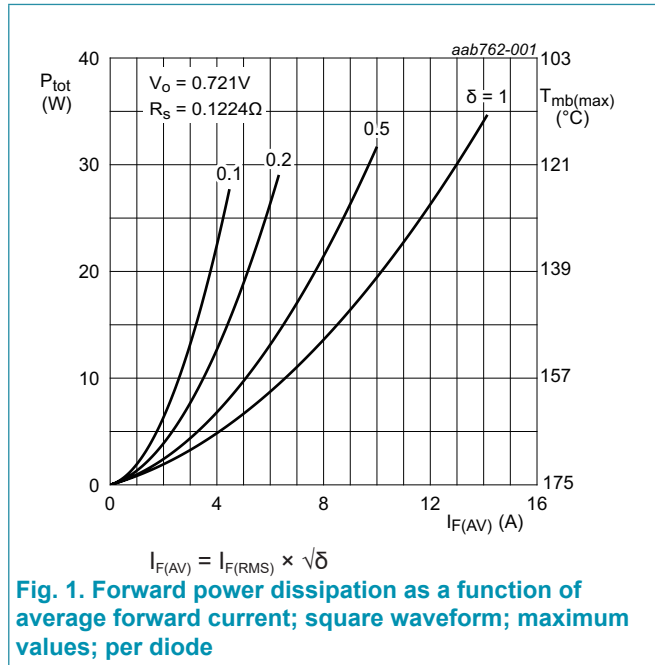
Type number	Marking codes
NXPSC20650W-A	NXPSC20650W-A

## 8. Limiting values

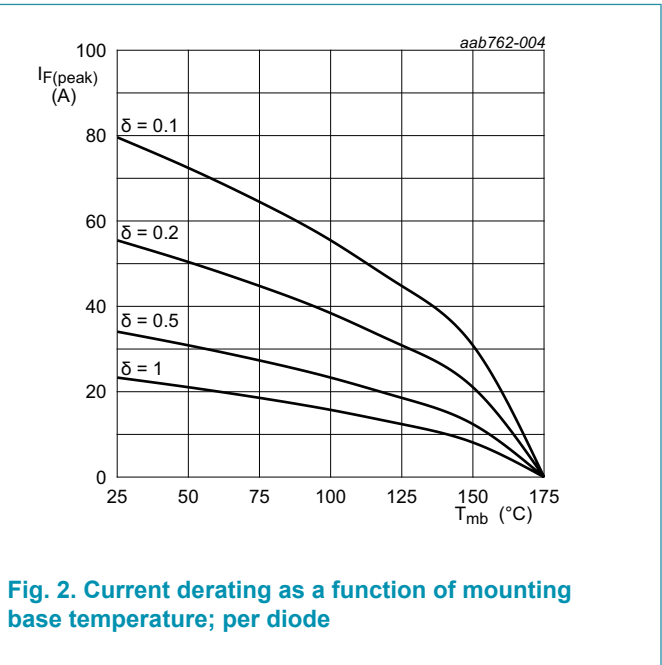
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		650	V
$V_{RWM}$	crest working reverse voltage		650	V
$V_R$	reverse voltage	DC	650	V
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25 \mu s$ ; $T_{mb} \leq 112 \text{ }^\circ\text{C}$ ; square-wave pulse; per diode	20	A
$I_{O(AV)}$	limiting average output current	$\delta = 0.5$ ; square-wave pulse; $T_{mb} \leq 105 \text{ }^\circ\text{C}$ ; both diodes conducting; Fig. 1; Fig. 2	20	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10 \text{ ms}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; sine-wave pulse; per diode	50	A
		$t_p = 10 \mu s$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; sine-wave pulse; per diode	450	A
$I^2t$	$I^2t$ for fusing	sine-wave pulse; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ ; per diode	12.5	A <sup>2</sup> s
$T_{stg}$	storage temperature		-55 to 175	$^\circ\text{C}$
$T_j$	junction temperature		175	$^\circ\text{C}$



**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode**

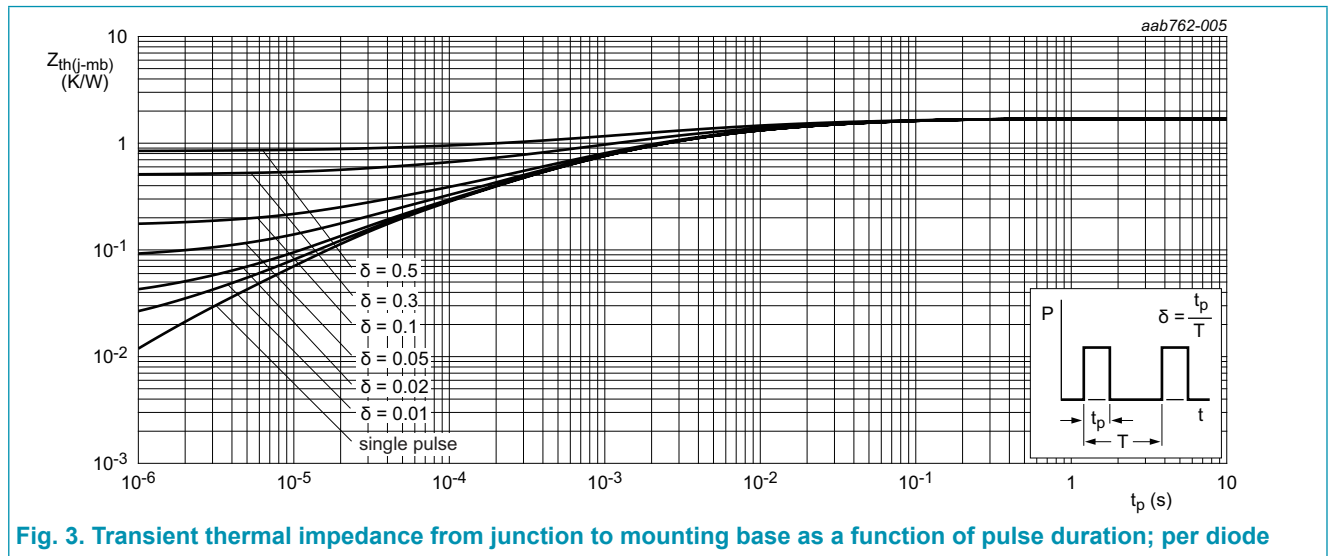


**Fig. 2. Current derating as a function of mounting base temperature; per diode**

## 9. Thermal characteristics

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Per diode; <a href="#">Fig. 3</a>	-	-	1.8	K/W
		both diodes conducting	-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

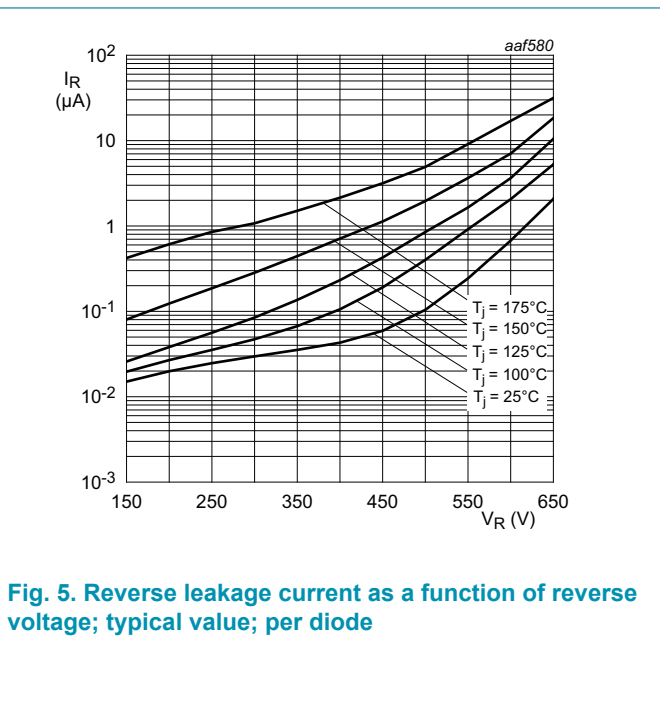
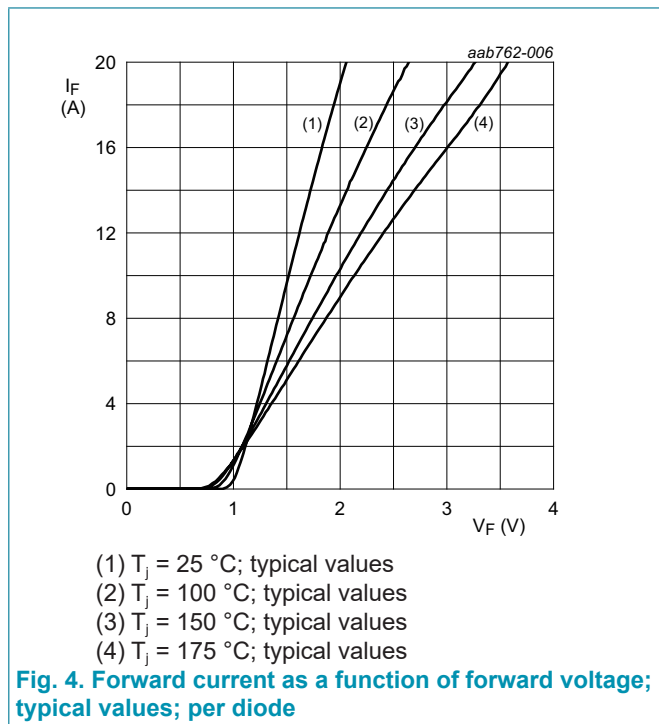


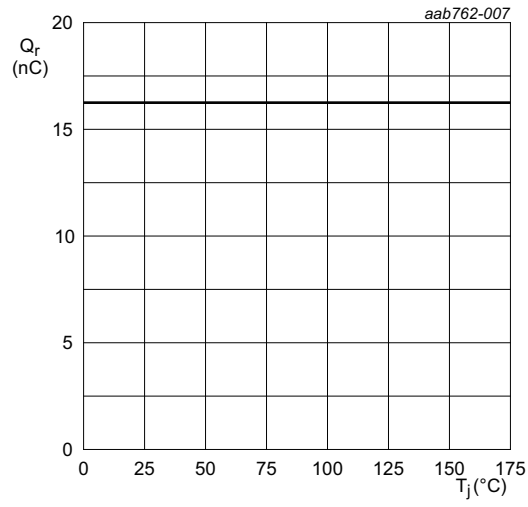
**Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration; per diode**

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward current	$I_F = 10\text{ A}; T_J = 25\text{ °C};$ per diode; <a href="#">Fig. 4</a>	-	1.5	1.7	V
		$I_F = 10\text{ A}; T_J = 150\text{ °C};$ per diode; <a href="#">Fig. 4</a>	-	1.8	2.1	V
$I_R$	reverse current	$V_R = 650\text{ V}; T_J = 25\text{ °C};$ per diode; <a href="#">Fig. 5</a>	-	-	60	$\mu\text{A}$
		$V_R = 650\text{ V}; T_J = 150\text{ °C};$ per diode; <a href="#">Fig. 5</a>	-	-	240	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 10\text{ A}; V_R = 400\text{ V}; dI_F/dt = 500\text{ A}/\mu\text{s};$ $T_J = 25\text{ °C};$ per diode; <a href="#">Fig. 6</a>	-	16	-	nC
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 1\text{ V}; T_J = 25\text{ °C};$ per diode	-	328	-	pF
		$f = 1\text{ MHz}; V_R = 300\text{ V}; T_J = 25\text{ °C};$ per diode	-	44	-	pF
		$f = 1\text{ MHz}; V_R = 600\text{ V}; T_J = 25\text{ °C};$ per diode	-	42	-	pF
$E_{as}$	non-repetitive avalanche energy	$I_R = 5.5\text{ A}; T_{J(\text{init})} = 25\text{ °C}; L = 5\text{ mH};$ per diode	75	-	-	mJ



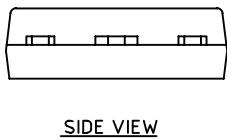
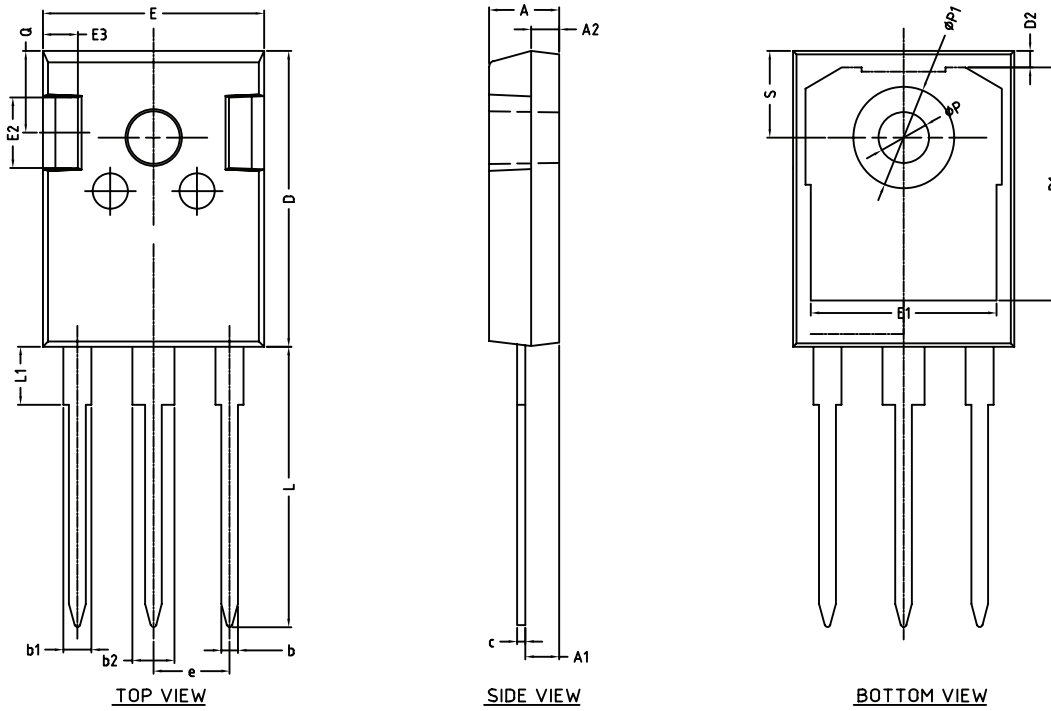


**Fig. 6. Recovered charge as a function of junction temperature; per diode**

### 11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247

SOT429N



UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	MAX	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	20.10	4.75	3.70	7.40	6.00	6.25
	MIN	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40	19.80	-	3.50	-	5.60	6.05

OUTLINE VERSION	REFERENCES			PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT429N		TO-247			

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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